

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process) (Bias Resistor built-in Transistor)

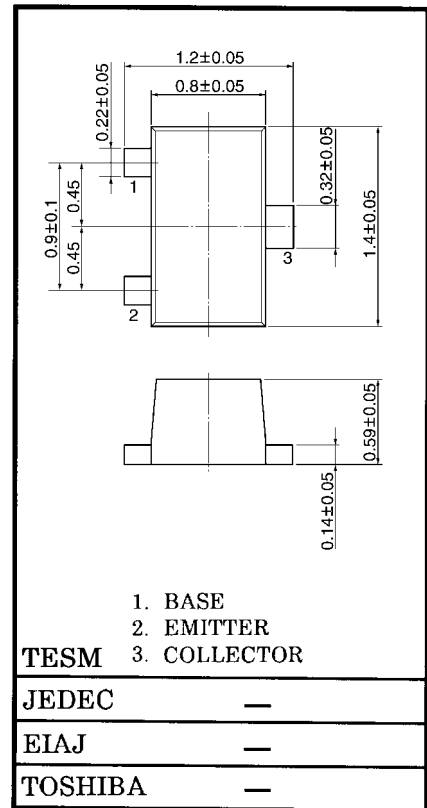
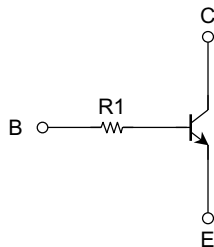
RN1112FT, RN1113FT

Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications.

Unit in mm

- High-density mount is possible because of devices housed in very thin TSM packages.
- Incorporating a bias resistor into a transistor reduces parts count. Reducing the parts count enable the manufacture of ever more compact equipment and save assembly cost.
- Wide range of resistor values are available to use in various circuit designs.
- Complementary to RN2112FT, RN2113FT

Equivalent Circuit and Bias Resistor Values



Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA
Collector power dissipation	P_C (Note)	100	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	–55~150	°C

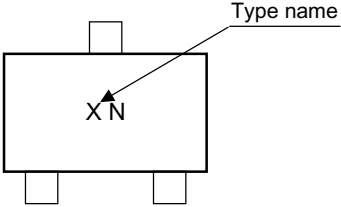
Note: Total rating

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Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		I_{CBO}	$V_{CB} = 50\text{ V}, I_E = 0$	—	—	100	nA
Emitter cut-off current		I_{EBO}	$V_{EB} = 5\text{ V}, I_C = 0$	—	—	100	nA
DC current gain		h_{FE}	$V_{CE} = 5\text{ V}, I_C = 1\text{ mA}$	120	—	700	
Collector-emitter saturation voltage		$V_{CE(sat)}$	$I_C = 5\text{ mA}, I_B = 0.25\text{ mA}$	—	0.1	0.3	V
Transition frequency		f_T	$V_{CE} = 10\text{ V}, I_C = 5\text{ mA}$	—	250	—	MHz
Collector output capacitance		C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	3	6	pF
Input resistor	RN1112FT	R1	—	15.4	22	28.6	kΩ
	RN1113FT			32.9	47	61.1	

Type Name	Marking
RN1112FT	
RN1113FT	